BC858CDXV6T1, BC858CDXV6T5

Dual General Purpose Transistor

PNP Dual

This transistor is designed for general purpose amplifier applications. It is housed in the SOT-563 which is designed for low power surface mount applications.

Features

• These are Pb-Free Devices

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-30	V
Collector - Base Voltage	V _{CBO}	-30	V
Emitter – Base Voltage	V _{EBO}	-5.0	V
Collector Current – Continuous	Ic	-100	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

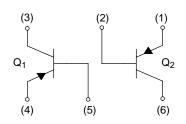
Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation, (Note 1) $T_A = 25^{\circ}C$ Derate above 25°C	P _D	357 2.9	mW mW/°C
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation, (Note 1) $T_A = 25^{\circ}C$ Derate above 25°C	P _D	500 4.0	mW mW/°C
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	250	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

^{1.} FR-4 @ Minimum Pad



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SOT-563 CASE 463A PLASTIC

MARKING DIAGRAMS



3L = Device Code M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC858CDXV6T1	SOT-563	4000/Tape & Reel
BC858CDXV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel
BC858CDXV6T5	SOT-563	8000/Tape & Reel
BC858CDXV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BC858CDXV6T1, BC858CDXV6T5

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	-			•	1
Collector – Emitter Breakdown Voltage (I _C = -10 mA)	V _(BR) CEO	-30	-	_	V
Collector – Emitter Breakdown Voltage ($I_C = -10 \mu A$, $V_{EB} = 0$)	V _(BR) CES	-30	_	_	V
Collector – Base Breakdown Voltage $(I_C = -10 \mu A)$	V _(BR) CBO	-30	_	_	V
Emitter – Base Breakdown Voltage $(I_E = -1.0 \mu A)$	V _{(BR)EBO}	-5.0	-	_	V
Collector Cutoff Current ($V_{CB} = -30 \text{ V}$) ($V_{CB} = -30 \text{ V}$, $T_A = 150^{\circ}\text{C}$)	Ісво		_ _	-15 -4.0	nA μA
ON CHARACTERISTICS		•	•		•
DC Current Gain $(I_C = -10 \mu\text{A}, V_{CE} = -5.0 \text{V})$ $(I_C = -2.0 \text{mA}, V_{CE} = -5.0 \text{V})$	h _{FE}	- 420	270 520	_ 800	-
Collector – Emitter Saturation Voltage ($I_C = -10$ mA, $I_B = -0.5$ mA) ($I_C = -100$ mA, $I_B = -5.0$ mA)	V _{CE(sat)}	_ _	_ _	-0.3 -0.65	V
Base – Emitter Saturation Voltage ($I_C = -10$ mA, $I_B = -0.5$ mA) ($I_C = -100$ mA, $I_B = -5.0$ mA)	V _{BE(sat)}	_ _	-0.7 -0.9	_ _	V
Base – Emitter On Voltage ($I_C = -2.0$ mA, $V_{CE} = -5.0$ V) ($I_C = -10$ mA, $V_{CE} = -5.0$ V)	V _{BE(on)}	-0.6 -	_ _	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS		•	•		•
Current – Gain – Bandwidth Product (I _C = –10 mA, V _{CE} = –5.0 Vdc, f = 100 MHz)	f⊤	100	-	_	MHz
Output Capacitance (V _{CB} = -10 V, f = 1.0 MHz)	C _{ob}	-	-	4.5	pF
Noise Figure (I _C = -0.2 mA, V _{CE} = -5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	-	_	10	dB

BC858CDXV6T1, BC858CDXV6T5

TYPICAL CHARACTERISTICS

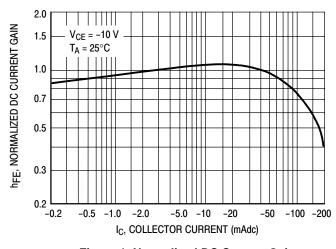


Figure 1. Normalized DC Current Gain

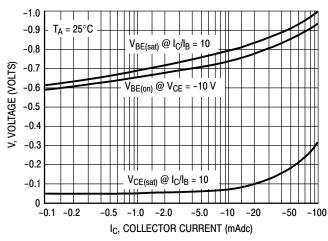


Figure 2. "Saturation" and "On" Voltages

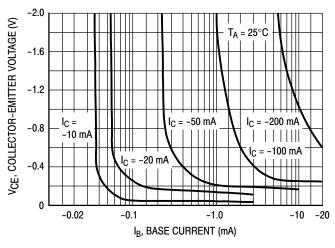


Figure 3. Collector Saturation Region

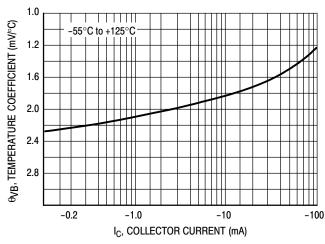


Figure 4. Base-Emitter Temperature Coefficient

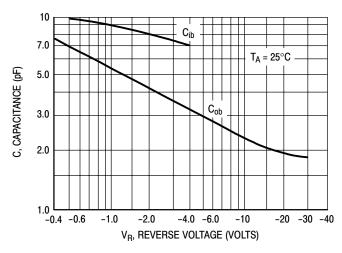


Figure 5. Capacitances

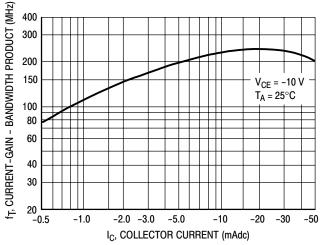


Figure 6. Current-Gain - Bandwidth Product

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



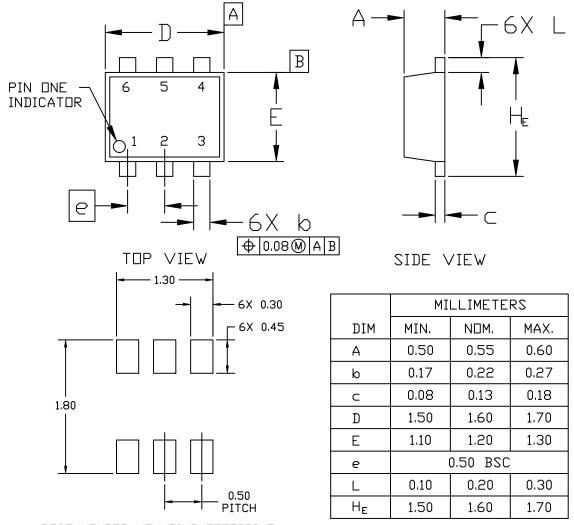


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NOTES:

- I. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



RECOMMENDED MOUNTING FOOTPRINT*

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

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DATE 26 JAN 2021

STYLE 1: PIN 1. EMITTER 1 2. BASE 1 3. COLLECTOR 2 4. EMITTER 2 5. BASE 2 6. COLLECTOR 1	STYLE 2: PIN 1. EMITTER 1 2. EMITTER 2 3. BASE 2 4. COLLECTOR 2 5. BASE 1 6. COLLECTOR 1	STYLE 3: PIN 1. CATHODE 1 2. CATHODE 1 3. ANODE/ANODE 4. CATHODE 2 5. CATHODE 2 6. ANODE/ANODE
STYLE 4: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 5: PIN 1. CATHODE 2. CATHODE 3. ANODE 4. ANODE 5. CATHODE 6. CATHODE	STYLE 6: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 7: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. ANODE 6. CATHODE	STYLE 8: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SDURCE 5. DRAIN 6. DRAIN	STYLE 9: PIN 1. SDURCE 1 2. GATE 1 3. DRAIN 2 4. SDURCE 2 5. GATE 2 6. DRAIN 1
STYLE 10: PIN 1. CATHODE 1 2. N/C 3. CATHODE 2 4. ANODE 2 5. N/C 6. ANODE 1	STYLE 11: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	

GENERIC MARKING DIAGRAM*



XX = Specific Device CodeM = Month Code= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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